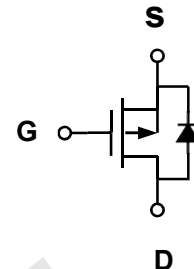




P-Channel Enhancement Mode Power MOSFET

Description

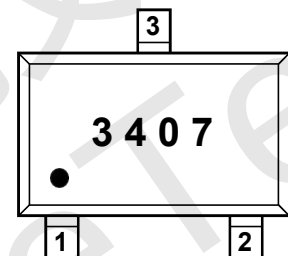
The MX3407A uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.



Schematic diagram

General Features

- ◆ $V_{DS} = -30V$, $I_D = -4.3A$
- ◆ $R_{DS(ON)}(Typ.) = 54m\Omega @ V_{GS} = -4.5V$
- ◆ $R_{DS(ON)}(Typ.) = 38m\Omega @ V_{GS} = -10V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package



Marking and pin assignment

Application

- ◆ PWM applications
- ◆ Load switch
- ◆ Power management



Sot-23 top view

Ordering Information

Part Number	Marking	Storage Temperature	Package	Devices Per Reel
MX3407A	XXXXX	-55°C to +150°C	SOT-23-3	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	V_{DS}	-30	V
Gate-source voltage	V_{GS}	± 20	V
Drain current-continuous Drain Current-Pulsed (Note 1)	I_D	-4.3	A
	I_{DM}	-20	A
Drain-source Diode forward current	I_S	-1.25	A
Maximum power dissipation	P_D	1	W
Operating junction Temperature range	T_j	-55—150	°C



Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF Characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-30	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V	-	-	-1	μA
Gate-body leakage	I _{GSS}	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
ON Characteristics						
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-3	V
Drain-source on-state resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-4.1A	-	38	52	mΩ
		V _{GS} =-4.5V, I _D =-4A	-	54	90	mΩ
Forward transconductance	g _{fs}	V _{GS} =-5V, I _D =-4.1A	-5.5	-	-	V
Dynamic Characteristics						
Input capacitance	C _{ISS}	V _{DS} =-15V ,V _{GS} =0V f=1.0MHz	-	700	-	pF
Output capacitance	C _{OSS}		-	120	-	
Reverse transfer capacitance	C _{RSS}		-	75	-	
Switching Characteristics						
Turn-on delay time	t _{D(ON)}	V _{DD} =-15V V _{GEN} =-10V R _L =3.6ohm R _{GEN} =3ohm	-	9	-	ns
Rise time	tr		-	5	-	
Turn-off delay time	t _{D(OFF)}		-	28	-	
Fall time	tf		-	13.5	-	
Total gate charge	Qg	V _{DS} =-15V,I _D =-4A V _{GS} =-10V	-	14	-	nC
Gate-source charge	Qgs		-	3.1	-	
Gate-drain charge	Qgd		-	3.	-	
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode forward voltage	V _{SD}	V _{GS} =0V,I _s =-1A	-	-	-1.2	V

otes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to product



Typical Performance Characteristics

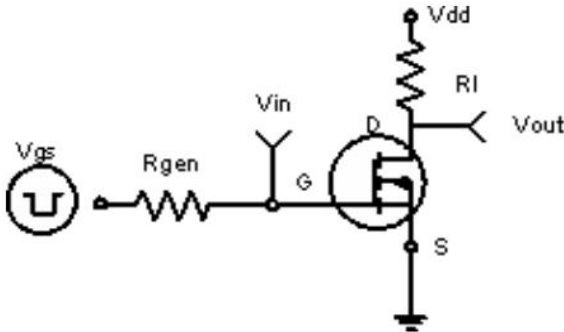


Figure 1: Switching Test Circuit

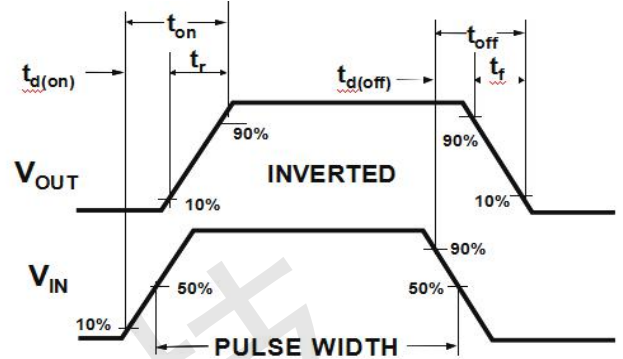


Figure 2: Switching Waveforms

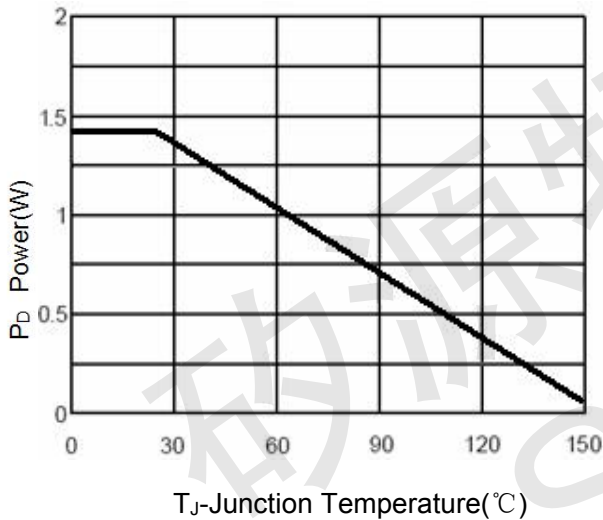


Figure 3 Power Dissipation

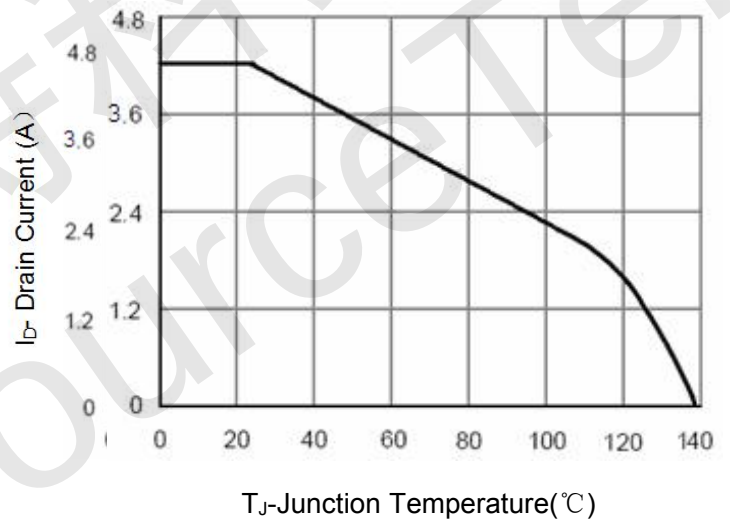


Figure 4 Drain Current

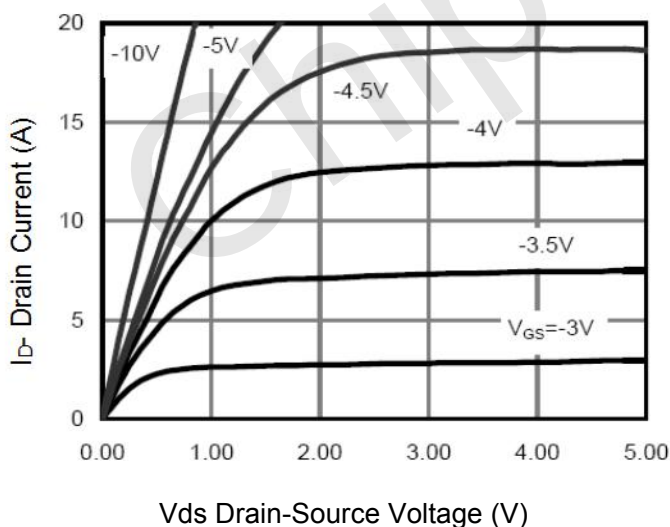


Figure 5 Output CHARACTERISTICS

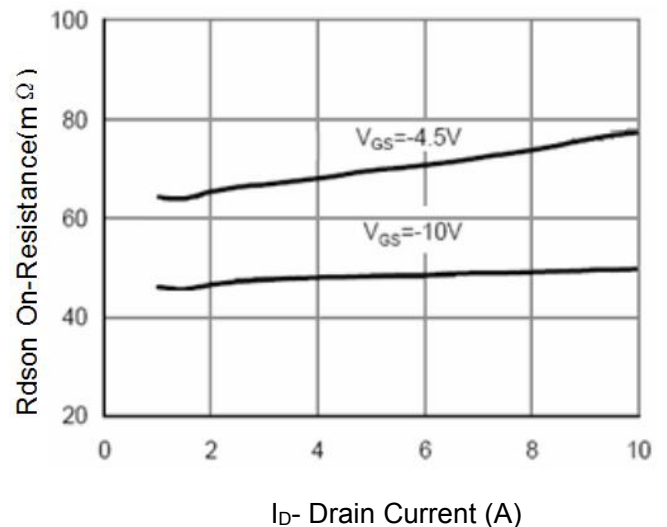


Figure 6 Drain-Source On-Resistance

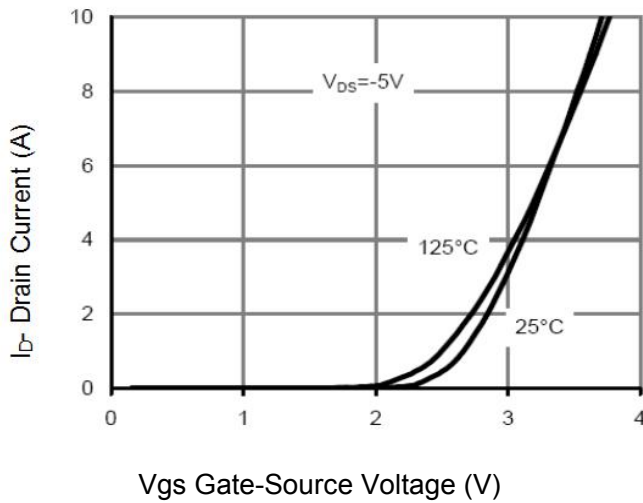


Figure 7 Transfer Characteristics

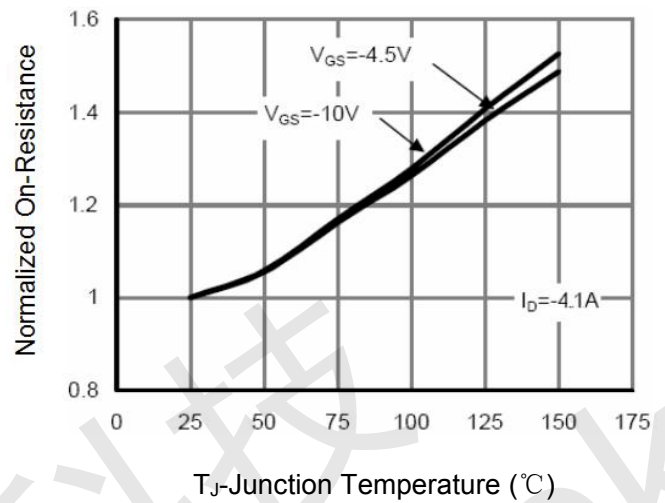


Figure 8 Drain-Source On-Resistance

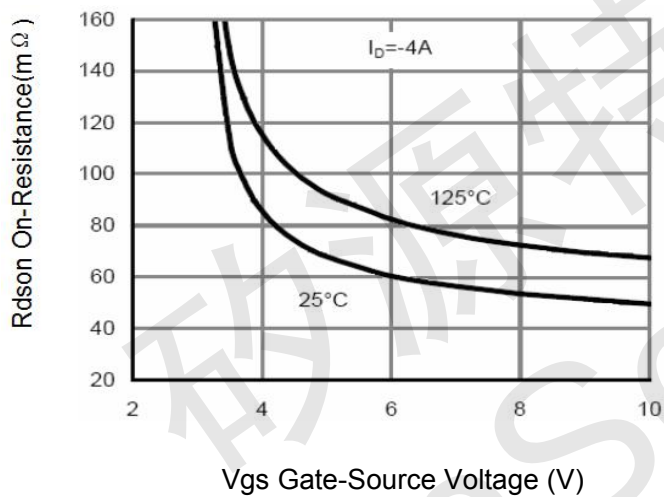


Figure 9 Rdson vs Vgs

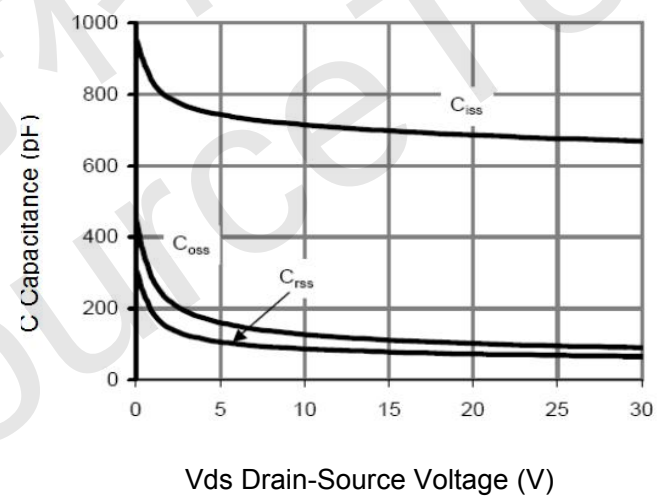


Figure 10 Capacitance vs Vds

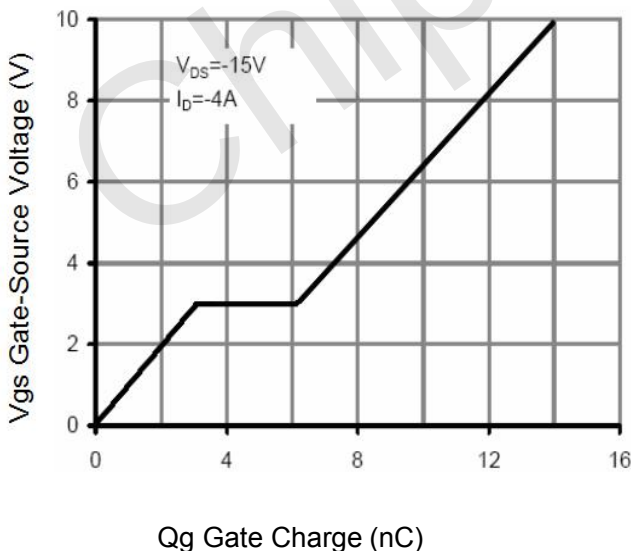


Figure 11 Gate Charge

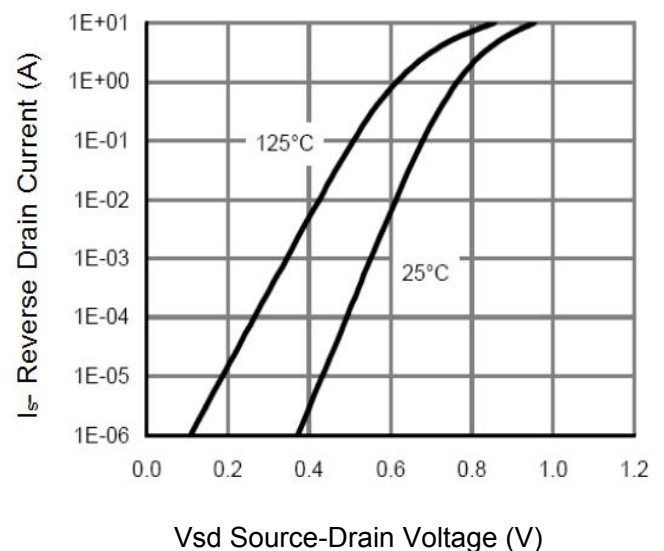


Figure 12 Source- Drain Diode Forward

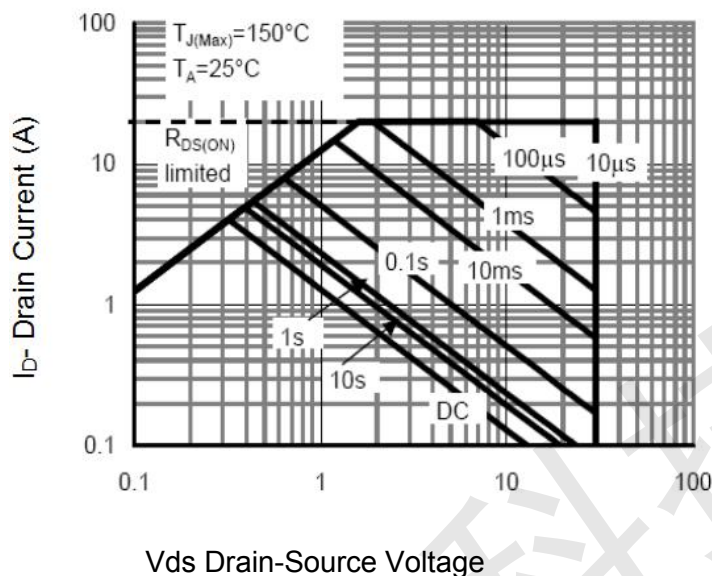


Figure 13 Safe Operation Area

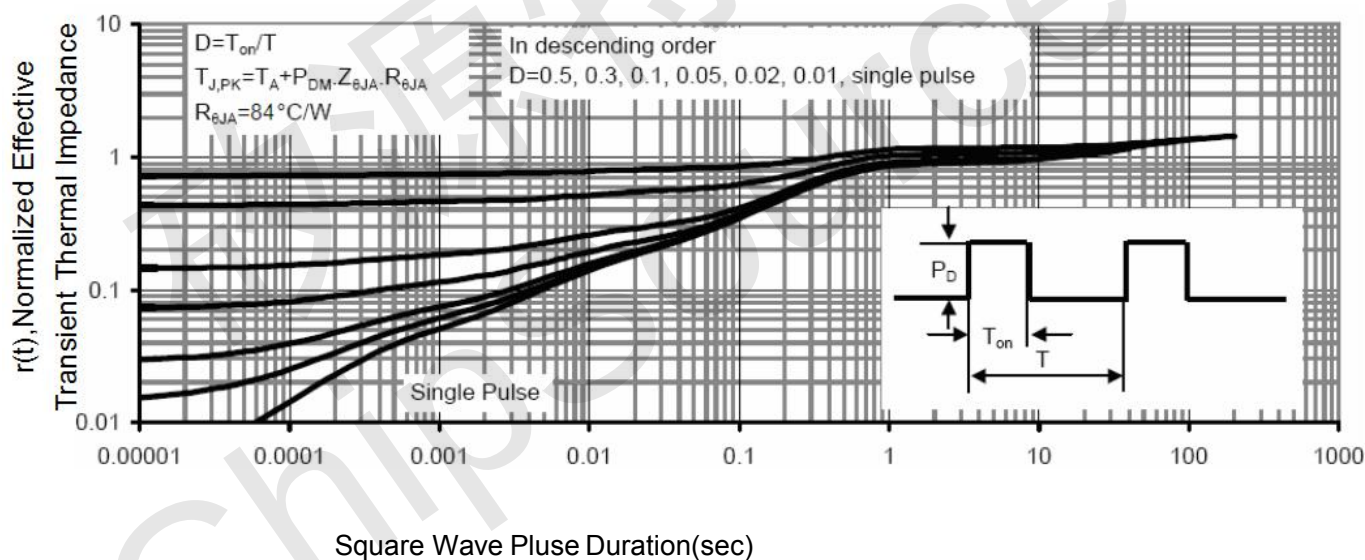
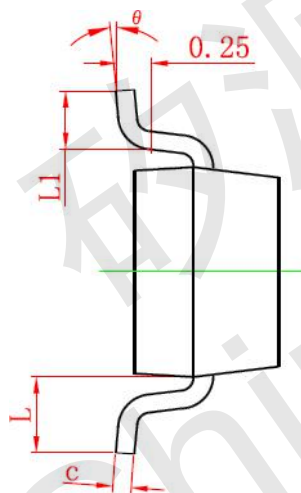
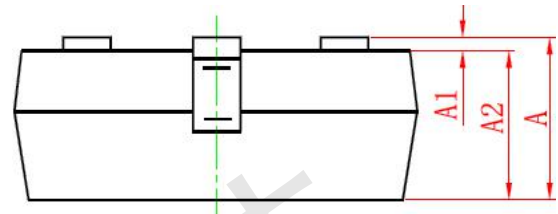
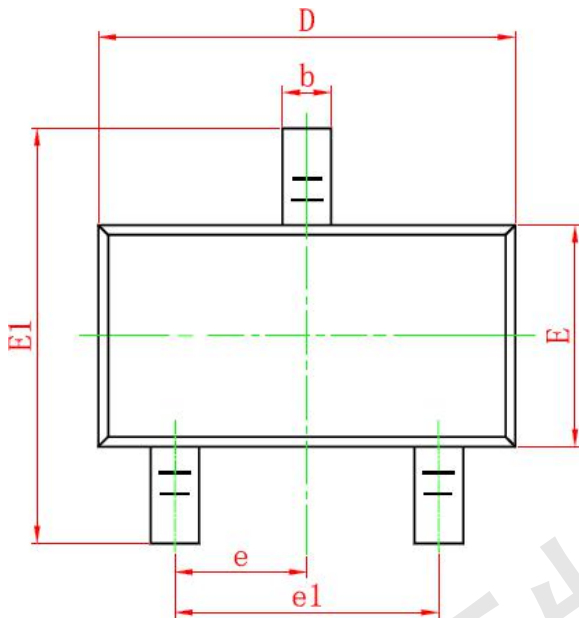


Figure 14 Normalized Maximum Transient Thermal Impedan



SOT-23 PACKAGE INFORMATION



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500